Substitute form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/849,617
				Filing Date	May 20, 2004
				First Named Inventor	Adam Saxler
				Group Art Unit	2822
(use as many sheets as necessary)				Examiner Name	~~Alan Carlson~~ K. DUONG
Sheet	1	of	1	Attorney Docket Number	5308-413

OIPE JC37 JUL 13 2005 PATENT & TRADEMARK OFFICE

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Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
KBD	1.	US-5,990,531		Taskar et al.	11-23-1999
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OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
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Examiner Signature		Date Considered	4/5/2006

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				Group Art Unit	2822
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

Complete if Known	
Application Number	10/849,617
Filing Date	May 20, 2004
First Named Inventor	Saxler et al.
Group Art Unit	2822
Examiner Name	~~Amir Zarabian~~
Attorney Docket Number	5308-413

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				Group Art Unit	2822
(use as many sheets as necessary)				Examiner Name	Abdur Zarabian
Sheet	2	of	3	Attorney Docket Number	5308-413

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Examiner Signature		Date Considered	4/5/2006

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/849,617
				Filing Date	May 20, 2004
				First Named Inventor	Saxler et al.
				Group Art Unit	2822
(use as many sheets as necessary)				Examiner Name	~~Mahmoud Dahimian~~
Sheet	3	of	3	Attorney Docket Number	5308-413

OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
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Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Attorney Docket No. 5308-412	Serial No. 10/849,5617
	Applicant: Saxler et al.	
	Filing Date: May 20, 2004	GAU: 2822

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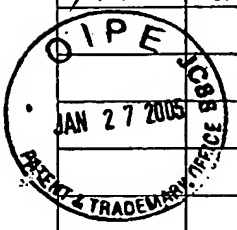
KBD	1.	5,592,501	1/7/97	Edmond et al.	372	45	



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		Document Number	Date	Country	Class	Subclass	Translation (Yes/No)

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Examiner: _____ Date Considered: 4/5/2006

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				First Named Inventor	Saxler
				Group Art Unit	~~2815~~
(use as many sheets as necessary)				Examiner Name	~~To Be Assigned~~
Sheet	A1	of	A1	Attorney Docket Number	5308-413

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				Group Art Unit	~~2811~~
(use as many sheets as necessary)				Examiner Name	~~To Be Assigned~~
Sheet	A2	of	A3	Attorney Docket Number	5308-392

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		Office	Number	Kind Code (if known)			
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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
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Examiner Signature		Date Considered	4/5/2006

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Substitute form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/849,617
				Filing Date	May 20, 2004
				First Named Inventor	Saxler
				Group Art Unit	~~2814~~
(use as many sheets as necessary)				Examiner Name	~~To Be Assigned~~
Sheet	A3	of	A3	Attorney Docket Number	5308-392

OTHER NON PATENT LITERATURE DOCUMENTS			
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	87.	United States Patent Application entitled "Methods of Having Laterally Grown Active Region and Methods of Fabricating Same," filed July 26, 2004 (Attorney Docket No. 5308-374).	
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